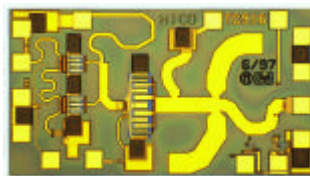


Agilent HMMC-5032 17.7-32 GHz Amplifier

Data Sheet



Chip Size:	1.4 × 0.78 mm (55.1 × 30.7 mils)
Chip Size Tolerance:	±10 μm (± 0.4 mils)
Chip Thickness:	127 ± 15 μm (5.0 ± 0.6 mils)
Pad Dimensions:	80 × 80 μm (3.2 × 3.2 mils)

Features

- 22 dBm Output P_(-1dB)
- 8 dB Gain
- 50Ω Input/Output Matching
- Small Size
- Bias: 4.5 Volts, 250 mA

Description

The HMMC-5032 is a MMIC power amplifier designed for use in wireless transmitters that operate within the 17.7 GHz to 32 GHz range. It provides 22 dBm of output power and 8 dB of small-signal gain from a small easy-to-use device. The HMMC-5032 was designed to be driven by the HMMC-5040 (20–40 GHz) or the HMMC-5618 (5.9–20 GHz) MMIC amplifier for linear transmit applications. This device has input and output matching circuitry for use in 50 ohm environments.

Absolute Maximum Ratings^[1]

Symbol	Parameters/Conditions	Min.	Max.	Units
V _{D1,2}	Drain Supply Voltages		5	Volts
V _{G1,2}	Gate Supply Voltages	-3.0	0.5	Volts
Det.Bias	Applied Detector Bias (Optional)		5	Volts
I _{DD}	Total Drain Current		460	mA
P _{in}	RF Input Power		23	dBm
T _{ch}	Channel Temperature ^[2]		170	°C
T _A	Backside Ambient Temperature	-55	+95	°C
T _{st}	Storage Temperature	-65	+170	°C
T _{max}	Maximum Assembly Temperature		300	°C

1. Absolute maximum ratings for continuous operation unless otherwise noted.

2. Refer to *DC Specifications / Physical Properties* table for derating information.

DC Specifications/Physical Properties^[1]

Symbol	Parameters/Conditions	Min.	Typ.	Max.	Units
$V_{D1,2}$	Drain Supply Operating Voltages	2	4.5	5	Volts
I_{D1}	First Stage Drain Supply Current ($V_{DD} = 4.5\text{ V}$, $V_{G1} \cong -0.8\text{ V}$)		100	140	mA
I_{D2}	Second Stage Drain Supply Current ($V_{DD} = 4.5\text{ V}$, $V_{GG} \cong -0.8\text{ V}$)		150	320	mA
$V_{G1,2}$	Gate Supply Operating Voltages ($I_{DD} \cong 250\text{ mA}$)		-0.8		Volts
V_P	Pinch-off Voltage ($V_{DD} = 4.5\text{ V}$, $I_{DD} \leq 10\text{ mA}$)	-2	-1.2		Volts
Det. Bias	Detector Bias Voltage (Optional)		$V_{D1,2}$	5	Volts
θ_{ch-bs}	Thermal Resistance ^[2] (Channel-to-Backside at $T_{ch} = 160^\circ\text{C}$)		67		$^\circ\text{C}/\text{Watt}$
T_{ch}	Channel Temperature ^[3] ($T_A = 85^\circ\text{C}$, MTTF > 10^6 hrs $V_{DD} = 4.5\text{ V}$, $I_{DD} = 250\text{ mA}$)		160		$^\circ\text{C}$

Notes:

1. Backside ambient operating temperature $T_A = 25^\circ\text{C}$ unless otherwise noted.
2. Thermal resistance ($^\circ\text{C}/\text{Watt}$) at a channel temperature $T(^\circ\text{C})$ can be *estimated* using the equation:

$$\theta(T) \cong \theta_{ch-bs} \times [T(^\circ\text{C})+273] / [160^\circ\text{C}+273].$$
3. Derate MTTF by a factor of two for every 8°C above T_{ch} .

RF Specifications

($T_A = 25^\circ\text{C}$, $Z_0 = 50\Omega$, $V_{DD} = 4.5\text{ V}$, $I_{DD} = 250\text{ mA}$)

Symbol	Parameters/Conditions	Low Band Specifications			Upper Band Specifications			Units
		Min.	Typ.	Max.	Min.	Typ.	Max.	
BW	Operating Bandwidth	17.7		26.5	25		31.5	GHz
Gain	Small Signal Gain	7	8		6	7		dB
$\Delta\text{Gain}/\Delta T$	Temperature Coefficient of Gain		0.02			0.02		dB/ $^\circ\text{C}$
$P_{-1\text{dB}}$	Output Power at 1dB Gain Compression	21	22		21	22		dBm
P_{SAT}	Saturated Output Power ^[1]		24			24		dBm
$(RL_{in})_{\text{MIN}}$	Minimum Input Return Loss	8	9		10	15		dB
$(RL_{out})_{\text{MIN}}$	Minimum Output Return Loss	9	10		15	20		dB
Isolation	Minimum Reverse Isolation		35			30		dB

Notes:

1. Devices operating continuously beyond 1 dB gain compression may experience power degradation.

Applications

The HMMC-5032 MMIC is a broadband power amplifier designed for use in transmitters that operate in various frequency bands between 17.7 GHz and 32 GHz. It can be attached to the output of the HMMC-5040 (20–40 GHz) or the HMMC-5618 (5.9–20 GHz) MMIC amplifier, increasing the power handling capability of transmitters requiring linear operation.

Biasing and Operation

The recommended DC bias condition is with both drains (V_{D1} and V_{D2}) connected to single 4.5 volt supply and both gates (V_{G1} and V_{G2}) connected to an adjustable negative voltage supply. The gate voltage is adjusted for a total drain supply current of typically 250 mA.

The RF input and output are AC-coupled.

An optional output power detector network is also provided. Detector sensitivity can be adjusted by biasing the diodes

with typically 1 to 5 volts applied to the Det-Bias terminal. Simply connecting Det-Bias to the V_{D2} supply is a convenient method of biasing this detector network. The differential voltage between the Det-Ref and Det-Out bonding pads can be correlated to the RF power emerging from the RF Output port.

No ground wires are needed because ground connections are made with plated through-holes to the backside of the device.

Assembly Techniques

It is recommended that the electrical connections to the bonding pads be made using 0.7–1.0 mil diameter gold wire. The microwave/millimeter-wave connections should be kept as short as possible to minimize inductance. For assemblies requiring long bond wires, multiple wires can be attached to the RF bonding pads.

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of

storage, handling, and assembly.

MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.

Agilent application note #54, "GaAs MMIC ESD, Die Attach and Bonding Guidelines" provides basic information on these subjects.

Additional References:

PN# 3, "HMMC-5040 and HMMC-5032 Demo, 20–32 GHz High Gain Medium Power Amp," and PN# 4, "HMMC-5032 Intermodulation Distortion."

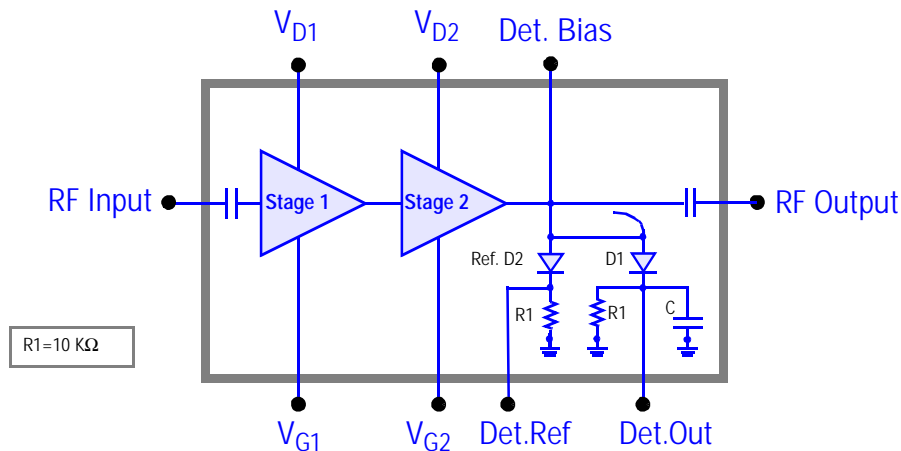


Figure 1.
Simplified Schematic Diagram

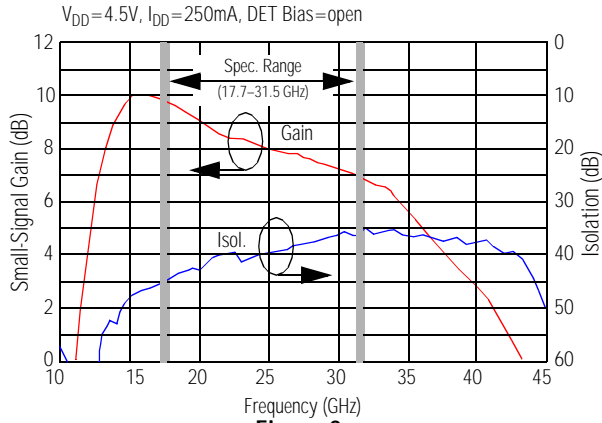


Figure 2.
Gain and Isolation vs. Frequency

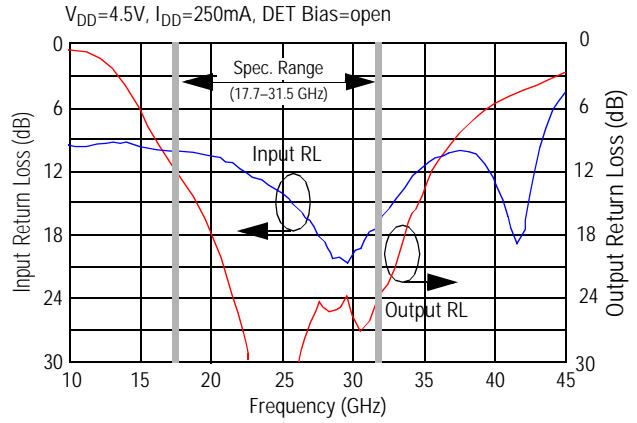


Figure 3.
Input and Output Return Loss vs. Frequency

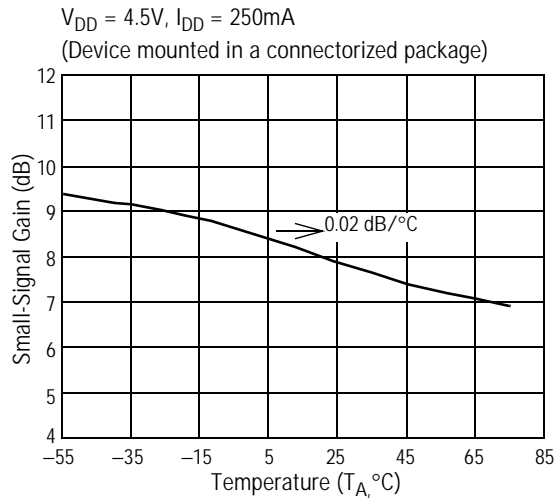


Figure 4.
Gain vs. Temperature

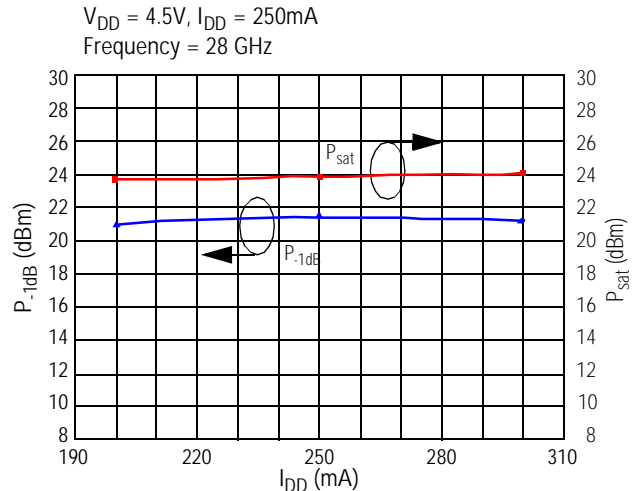


Figure 5.
Output Power vs. Total Drain Current

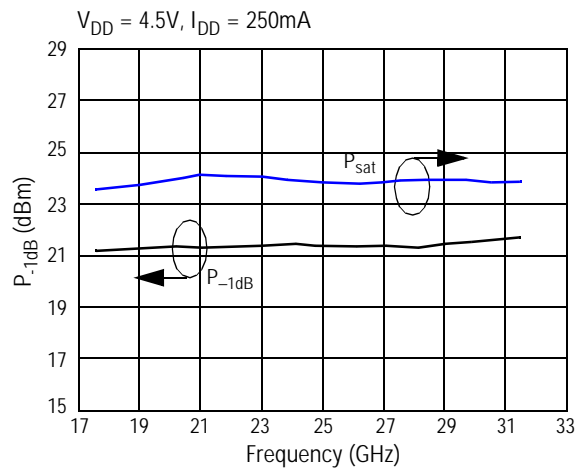


Figure 6.
Output Power vs. Frequency

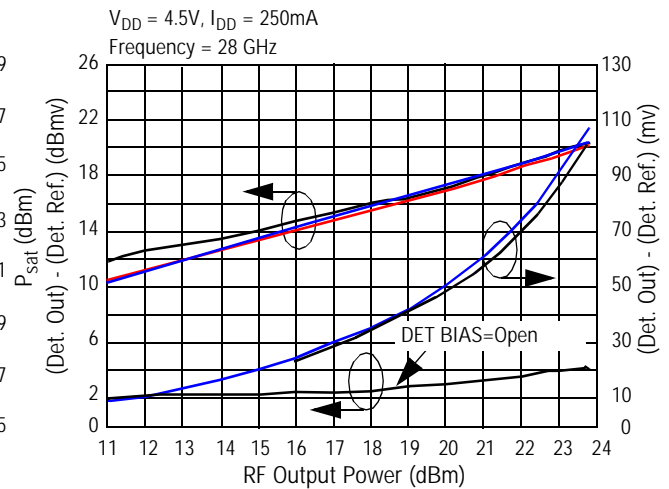


Figure 7.
Detector Voltages vs. Output Power for Various Detector Bias Voltages

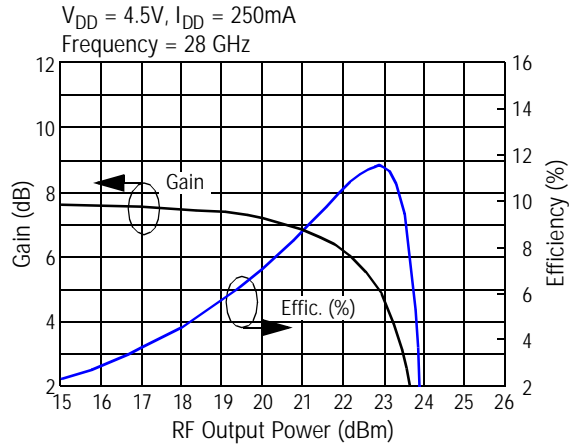


Figure 8.
Gain Compression and Efficiency vs. Power Out

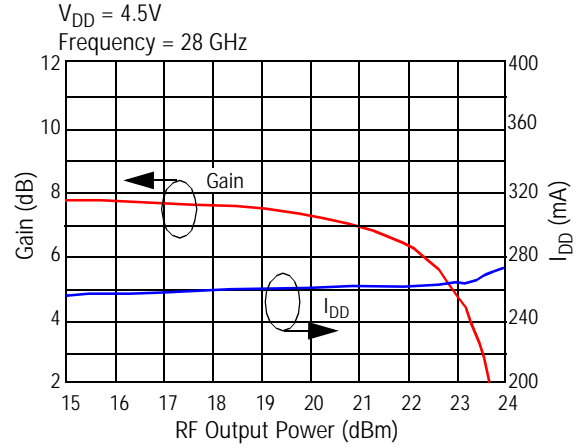


Figure 9.
Gain and Total Drain Current vs. Output Power

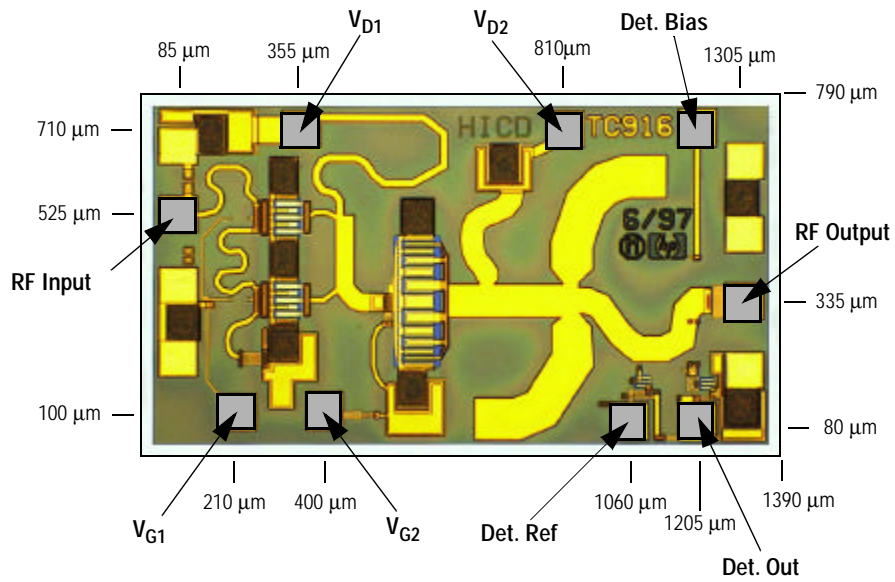


Figure 10.
Bonding Pad Locations

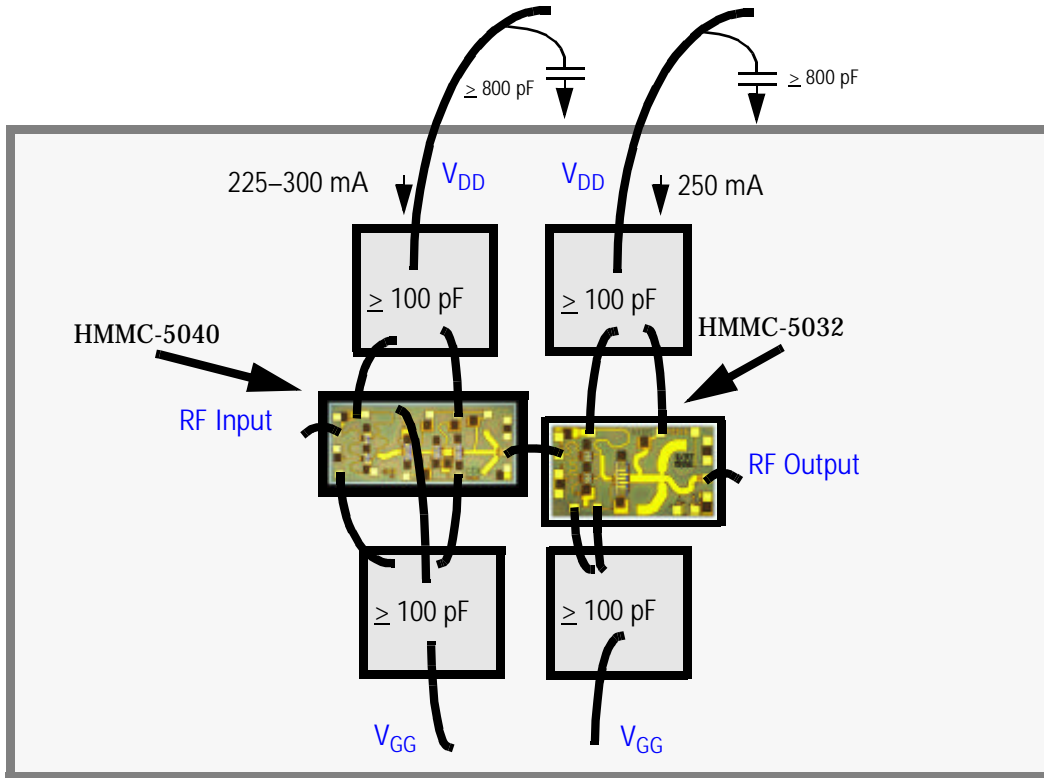


Figure 11.
 Assembly Diagram Illustrating the HMMC-5032 Cascaded
 with the HMMC-5040 for 20-32 GHz Applications

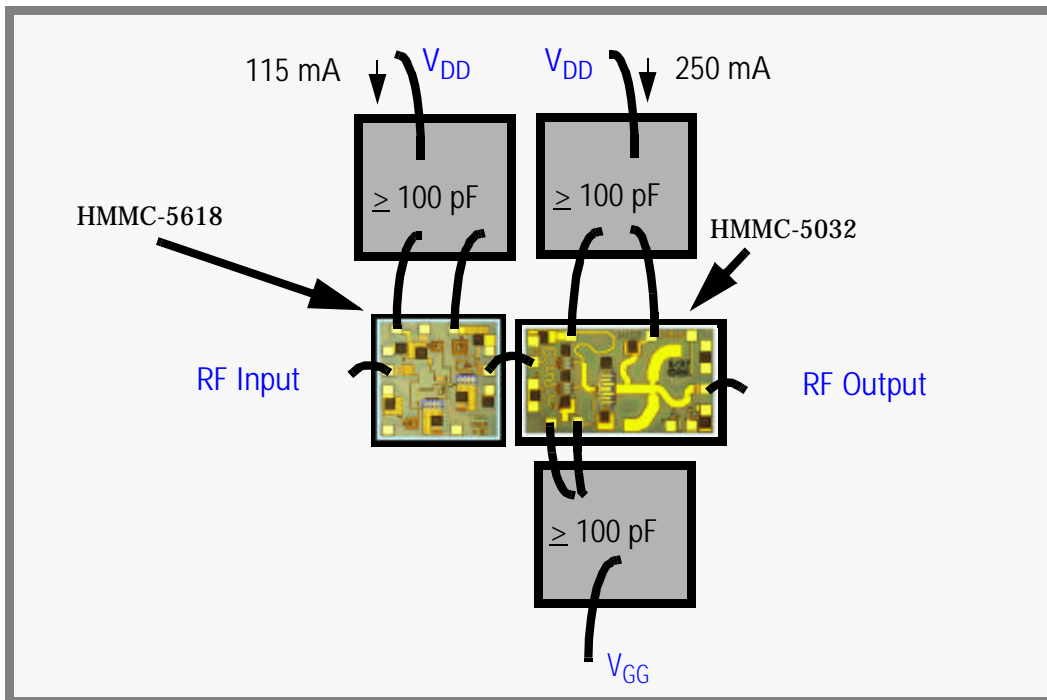


Figure 12.
 Assembly Diagram Illustrating the HMMC-5032 Cascaded
 with the HMMC-5618 for 17.7-20 GHz Applications

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local Agilent Technologies' sales representative.

www.agilent.com/semiconductors

For product information and a complete list of distributors, please go to our web site.

For technical assistance call:

Americas/Canada: +1 (800) 235-0312 or
(408) 654-8675

Europe: +49 (0) 6441 92460

China: 10800 650 0017

Hong Kong: (+65) 6271 2451

India, Australia, New Zealand: (+65) 6271 2394

Japan: (+81 3) 3335-8152(Domestic/International), or
0120-61-1280(Domestic Only)

Korea: (+65) 6271 2194

Malaysia, Singapore: (+65) 6271 2054

Taiwan: (+65) 6271 2654

Data subject to change.

Copyright ©2002 Agilent Technologies, Inc.

Obsoletes 5966-4572E

August 30, 2002

5988-2710EN



Agilent Technologies

